

METHOD FOR FORMING GUARD RING REGION OF SEMICONDUCTOR SUBSTRATE

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Inventor(s): SUZUKI YUJI
Applicant(s): MATSUSHITA ELECTRIC WORKS LTD
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Abstract

PURPOSE: To provide a method for forming a guard ring region having a sufficient field effect alleviating function on a semiconductor substrate in a short processing time.

CONSTITUTION: After an impurity diffused region 5 for a guard ring region is formed on an inner surface of a groove of a semiconductor substrate 1 having the groove 3 formed at a place where the ring region is to be formed by anisotropically etching, the substrate is oxidized, the oxide film covering at least the inner surface of the groove is removed, and then an oxide film 9 is again formed on the inner surface of the groove.

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